



2SK3703 — N-Channel Silicon MOSFET

General-Purpose Switching Device Applications

Features

- Low ON-resistance.
- 4V drive.
- Ultrahigh-speed switching.
- Motor drive, DC / DC converter.
- Avalanche resistance guarantee.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		60	V
Gate-to-Source Voltage	V _{GSS}		±20	V
Drain Current (DC)	I _D		30	A
Drain Current (Pulse)	I _{DP}	PW≤10μs, duty cycle≤1%	120	A
Allowable Power Dissipation	P _D		2.0	W
		T _c =25°C	25	W
Channel Temperature	T _{ch}		150	°C
Storage Temperature	T _{stg}		-55 to +150	°C
Avalanche Energy (Single Pulse) *1	E _{AS}		135	mJ
Avalanche Current *2	I _{AV}		30	A

Note : *1 V_{DD}=20V, L=200μH, I_{AV}=30A

*2 L≤200μH, Single pulse

Electrical Characteristics at Ta=25°C

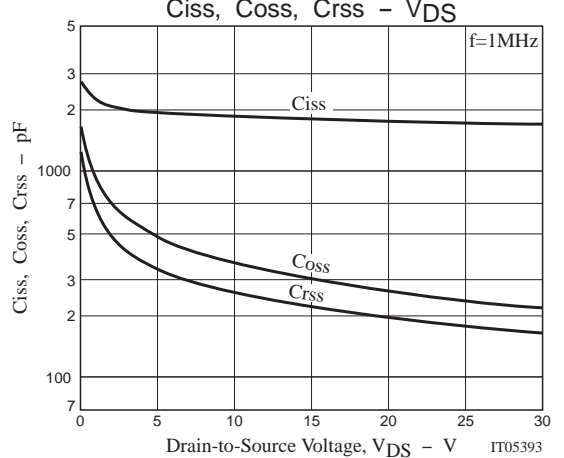
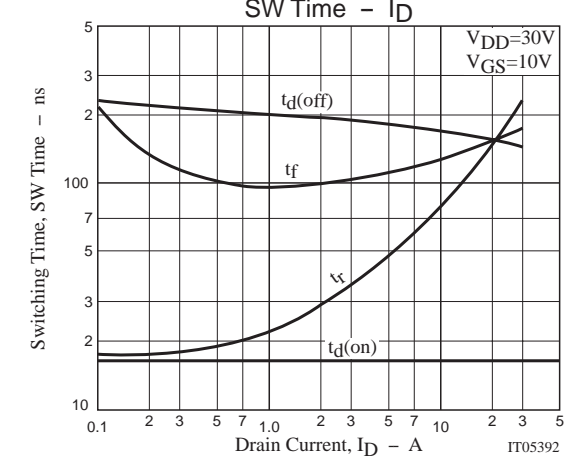
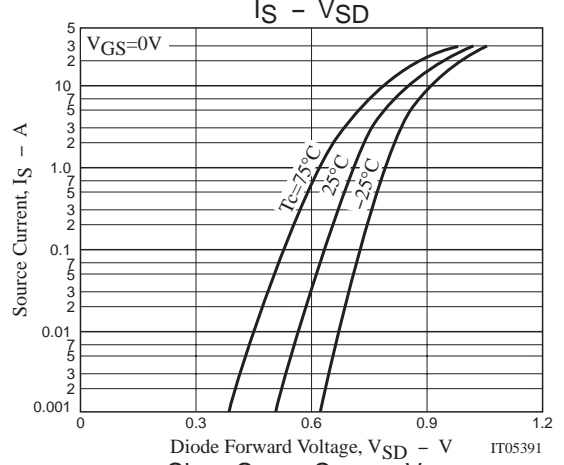
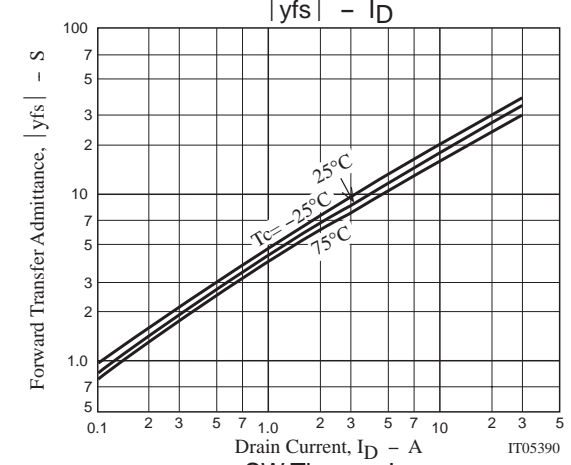
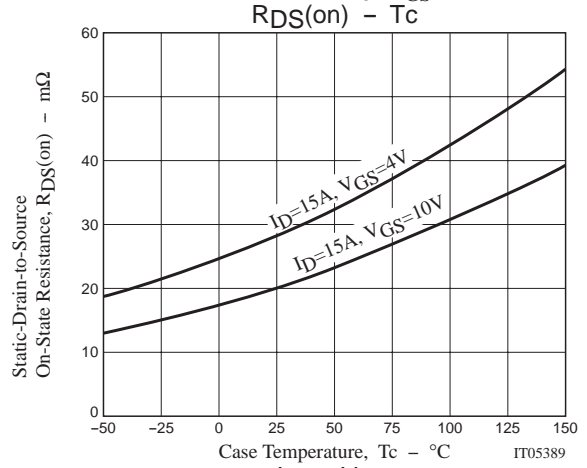
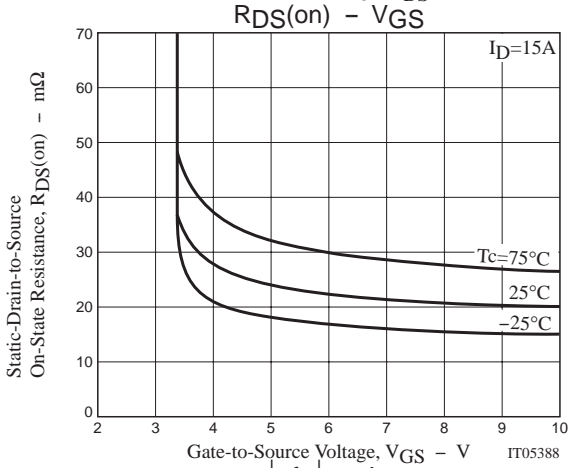
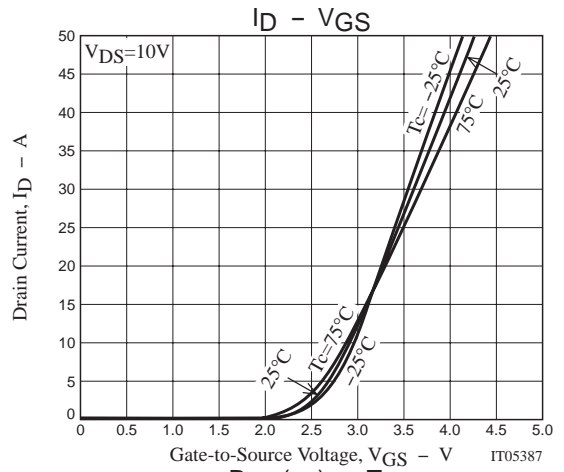
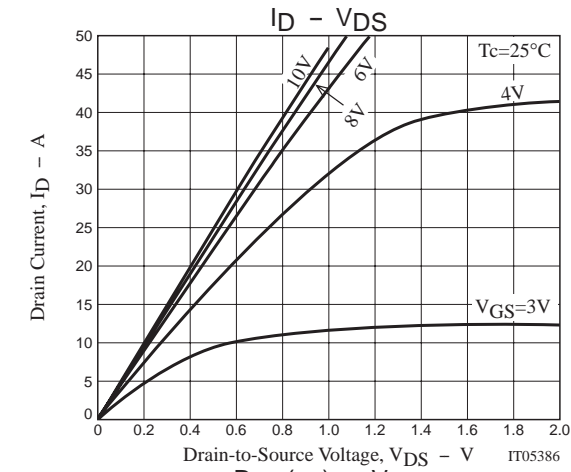
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V(BR)DSS	I _D =1mA, V _{GS} =0V	60			V
Zero-Gate Voltage Drain Current	I _{DSS}	V _{DS} =60V, V _{GS} =0V			1	μA
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} = ±16V, V _{DS} =0V			±10	μA
Cutoff Voltage	V _{GS(off)}	V _{DS} =10V, I _D =1mA	1.2		2.6	V
Forward Transfer Admittance	y _{fs}	V _{DS} =10V, I _D =15A	13	22		S
Static Drain-to-Source On-State Resistance	R _{DS(on)1}	I _D =15A, V _{GS} =10V		20	26	mΩ
	R _{DS(on)2}	I _D =15A, V _{GS} =4V		28	40	mΩ

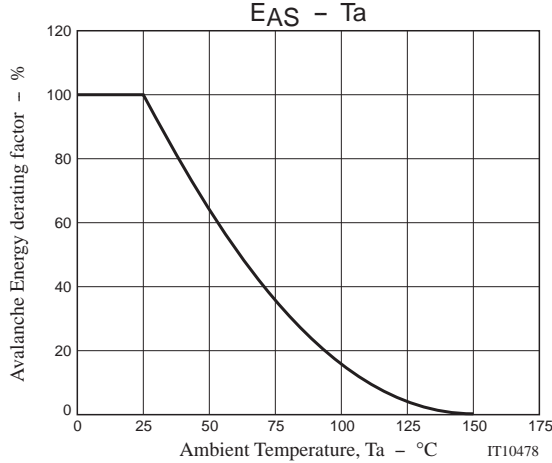
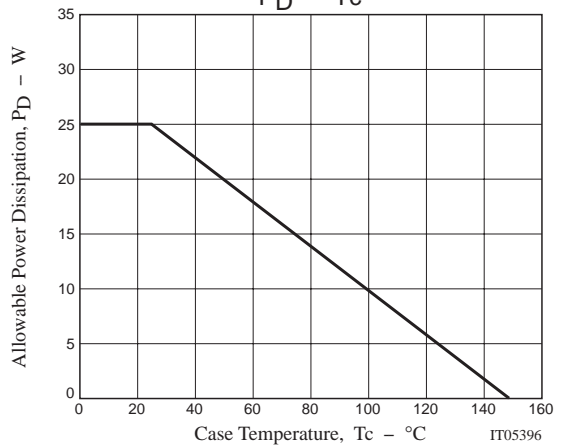
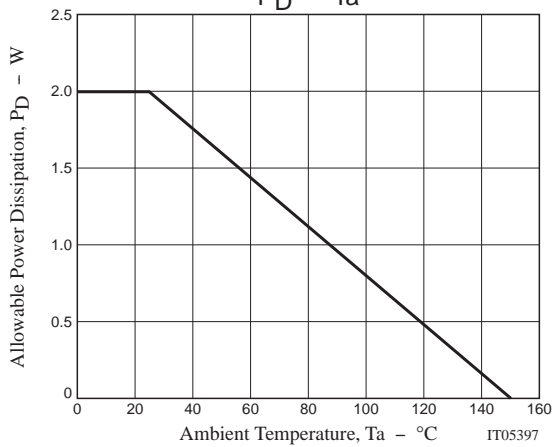
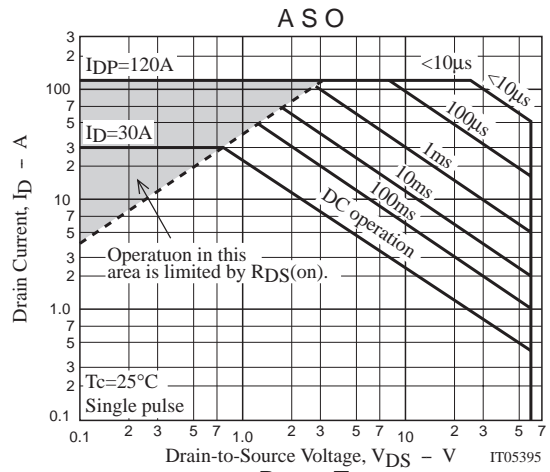
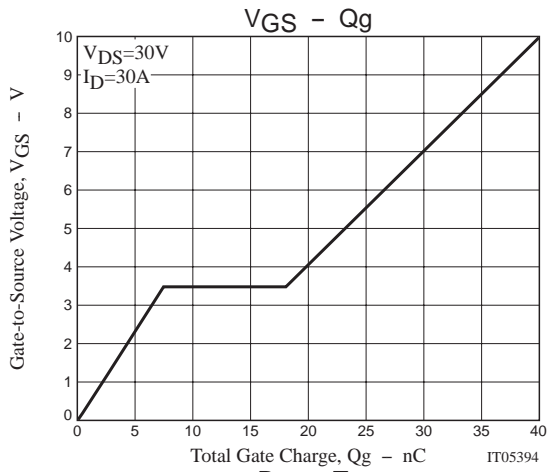
Marking : K3703

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Note on usage : Since the 2SK3703 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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